

## Silicon NPN Power Transistors

## 2SC2660 2SC2660A

## DESCRIPTION

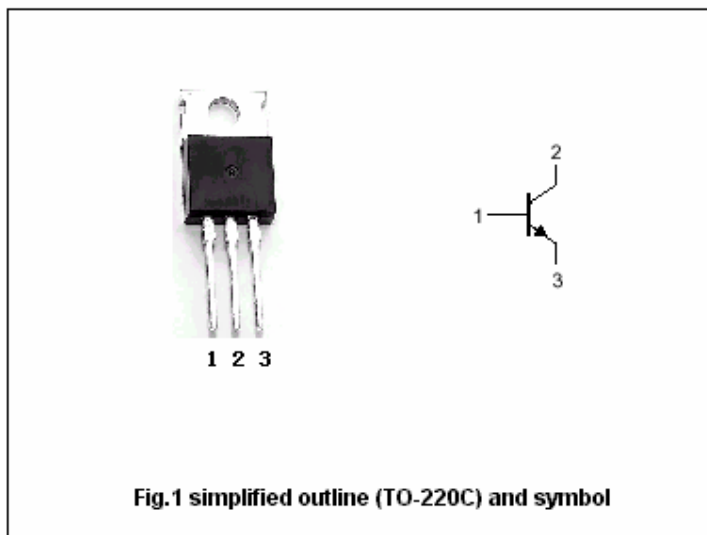
- With TO-220 package
- Complement to type 2SA1133/1133A
- High  $V_{CEO}$
- Large  $P_C$

## APPLICATIONS

- Power amplifier applications
- TV vertical deflection applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	200	V
$V_{CEO}$	Collector-emitter voltage	2SC2660	150	V
		2SC2660A	180	
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		2	A
$I_{CM}$	Collector current-peak		3	A
$P_C$	Collector power dissipation	$T_C=25$	30	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =0.5A ; I <sub>B</sub> =50m A			1.0	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V			1.0	V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SC2660	I <sub>C</sub> =5mA ; I <sub>B</sub> =0	150			V
		2SC2660A		180			
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage		I <sub>C</sub> =0.5mA ; I <sub>E</sub> =0	200			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage		I <sub>E</sub> =0.5mA ; I <sub>C</sub> =0	6			V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =200V ; I <sub>E</sub> =0			50	μ A
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =4V ; I <sub>C</sub> =0			50	μ A
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =0.15A ; V <sub>CE</sub> =10V	60		240	
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V	50			

◆ h<sub>FE-1</sub> classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE

